

2SB1462L

Silicon PNP epitaxial planer type

For general amplification

Complementary to 2SD2216L

■ Features

- High forward current transfer ratio h_{FE}
- Mold leadless type package, allowing downsizing and thinning of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

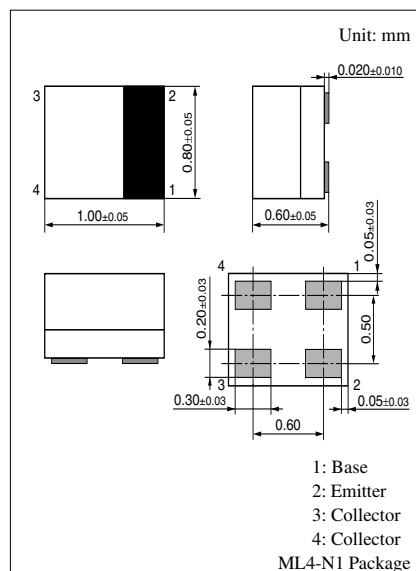
Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V_{CEO}	-50	V
Emitter to base voltage	V_{EBO}	-7	V
Peak collector current	I_{CP}	-200	mA
Collector current	I_C	-100	mA
Collector power dissipation *	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) *: Printed circuit board copper foil for collector portion

area: 20.0 mm² or more, thickness: 1.6 mm

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -20\text{ V}, I_E = 0$			- 0.1	μA
	I_{CEO}	$V_{CE} = -10\text{ V}, I_B = 0$			-100	μA
Collector to base voltage	V_{CBO}	$I_C = -10\text{ }\mu\text{A}, I_E = 0$	-60			V
Collector to emitter voltage	V_{CEO}	$I_C = -100\text{ }\mu\text{A}, I_B = 0$	-50			V
Emitter to base voltage	V_{EBO}	$I_E = -10\text{ }\mu\text{A}, I_C = 0$	-7			V
Forward current transfer ratio	h_{FE}	$V_{CE} = -10\text{ V}, I_C = -2\text{ mA}$	180		390	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{ mA}, I_B = -10\text{ mA}$		- 0.3	- 0.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$		2.7		pF
Transition frequency	f_T	$V_{CB} = -10\text{ V}, I_E = 1\text{ mA}, f = 200\text{ MHz}$		80		MHz



Marking Symbol: J